

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT				Atty Docket: 31869-178950		Application No.: Rule 53(b) Divisional of Application No. 69688-315 10728,851	
				Applicant Takuji YOSHIDA		Group Art: 2824	
				Filing Date Concurrently			
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub- Class	Filing Date
CD HN	AA	4,503,524	3/1985	McELROY	—	—	
CD HN	AB	4,769,787	9/1988	FURUSAWA et al.	—	—	
CD HN	AC	4,953,928	9/1990	ANDERSON et al.	—	—	
CD HN	AD	5,022,000	6/1991	TERASAWA et al.	—	—	
CD HN	AE	5,047,981	9/1991	GILL et al.	—	—	
CD HN	AF	5,077,691	12/1991	HADDAD et al.	—	—	
CD HN	AG	5,122,985	6/1992	SANTIN	—	—	
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub- Class	Trans- lation
CD HN	AH	5494	01/12/1984	JAPAN	—	—	
CD HN	AI	52300	02/28/1989	JAPAN	—	—	
	AJ						
OTHER (Including Author, Title, Date, Pertinent Pages, etc.)							
CD HN	AK	D'ARRIGO et al., 1989 IEEE International Solid-State Circuits Conference, pp. 132-133; Session 10: Non-Volatile Memories; Tham 10.3: "A 5V-Only 256k Bit CMOS Flash EEPROM."					
CD HN	AL	N. ANANTHA et al., "Electrically Erasable Floating Gate F.E.T. Mem. Cell, "IBM Tech. Discl. Bull., Vol. 17, No. 8, Jan. 1975, pp. 2311-2313.					
CD HN	AM	R. DOCKERTY, "Nonvol. Mem. Array w. Single Famos Dev. Per Cell, "IBM Tech. Discl. Bull., Vol. 17, No. 8, Jan. 1975, pp. 2314-2315.					
CD HN	AN	M. KIKUCHI et al., "A 2047-Bit-N-Channel Fully Decoded Electrically Writable/Erasable Nonvol. R.O.M., "1 ST European Solid State Circuits Conf. (ESSIRC) Kent, England, Sept. 2-5, 1975, pp. 66-67.					
Examiner SON DINH / HIEN NGUYEN					Date Considered 10/20/82 2/6/04		
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT				Atty Docket: 31869-178950		Rule 53(b) Divisional of Application No. 09/680,945 <div style="font-size: 1.5em; font-family: cursive;">10/728,851</div>	
				Applicant Takuji YOSHIDA			
				Filing Date Concurrently		Group Art: 2824	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date
HN	AA	5,134,449	7/1992	GILL et al.	257	321	—
HN	AB	5,146,106	9/1992	ANDERSON et al.	327	50	—
HN	AC	5,155,701	10/1992	KOMORI et al.	365	185.23	—
HN	AD	5,168,335	12/1992	D'ARRIGO et al.	365	185.06	—
HN	AE	5,177,705	1/1993	McELROY et al.	365	185.06	—
HN	AF	5,187,683	2/1993	GILL et al.	365	185.06	—
HN	AG	5,235,544	10/1993	CAYWOOD	365	185.06	—
HN	AH	5,265,052	11/1993	D'ARRIGO et al.	365	185.23	—
HN	AI	5,003,510	3/1991	KAMISAKI	365	189.01	—
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub-Class	Translation
	AJ						
	AK						
	AL						
OTHER (Including Author, Title, Date, Pertinent Pages, etc.)							
	AM						
	AN						
Examiner <div style="font-size: 1.5em; font-family: cursive;">HIEN NGUYEN</div>					Date Considered <div style="font-size: 1.5em; font-family: cursive;">2/6/04</div>		
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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT				Atty Docket: 31869-178950		Rule 53(b) Divisional of Application No. 09/680,345 <div style="font-size: 2em; font-family: cursive;">10/728,851</div>	
				Applicant Takuji YOSHIDA			
				Filing Date Concurrently		Group Art: 2824	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date
SN/HN	AA	5,781,476	7/14/1998	SEKI et al.	—	—	
HN	AB	5,844,842	12/1/1998	SEKI et al.	—	—	
HN	AC	5,917,752	7/29/1999	SEKI et al.	—	—	
HN	AD	5,949,715	9/7/1999	SEKI et al.	—	—	
HN	AE	5,959,894	9/28/1999	SEKI et al.	—	—	
HN	AF	5,991,200	9/23/1999	SEKI et al.	—	—	
SN HN	AG	6,016,273	1/18/2000	SEKI et al.	—	—	
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SN HN	AH	0 320 231	6/14/1989	Europe	—	—	
HN	AI	63-188896	08/04/1988	JP	—	—	
SN HN	AJ	01-105397	04/21/1989	JP	—	—	
	AK						
	AL						
	AM						
OTHER (Including Author, Title, Date, Pertinent Pages, etc.)							
HN	AN	Haddad, et al., "Degradations Due to Hole Trapping in Flash Memory Cells", IEEE Electron Device Letters, Vol. 10, No. 3, March 1989, pp. 117-119.					
	AO						
Examiner SON DINH HIEN NGUYEN					Date Considered 10/20/02 2/6/04		
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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT				Atty Docket: 31869-178950		Rule 53(b) Divisional of Application No. 09/680,318 <div style="font-size: 1.5em; font-family: cursive;">10/728,851</div>	
				Applicant Takuji YOSHIDA			
				Filing Date Concurrently		Group Art: 2824	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub- Class	Filing Date
HN	AA	4,823,318	4/1989	D'ARRIGO et al.	365	185.23	—
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub- Class	Trans- lation
HN	AJ	01-289282	11/21/1989	JP	—	—	
HN	AK	01-021795	01/25/1989	JP	—	—	
HN	AL	62-099997	05/09/1987	JP	—	—	
OTHER (Including Author, Title, Date, Pertinent Pages, etc.)							
	AM						
	AN						
Examiner <div style="font-size: 1.5em; font-family: cursive;">HIEN NGUYEN</div>					Date Considered <div style="font-size: 1.5em; font-family: cursive;">2/6/04</div>		
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(use as many sheets as necessary)

Sheet	1	of	1
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Application Number	10119120 101728,851
Filing Date	April 10, 2002
First Named Inventor	Takuji YOSHIDA
Group Art Unit	2824
Examiner Name	Son T. Dinh
Attorney Docket Number	31869-178950

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**Examiner
Signature**

HIEN NGUYEN

Date Considered

2/6/04

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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